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Tuning the structural and optical features of V_2O_5 nanostructured films by Bi-doping and γ -irradiation for smart window applications

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ABSTRACT

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Doping and radiation exposure are two of the most preferred stratagems for enhancing the efficiency of V_2O_5 for optoelectronic and smart window applications. This work studies the effect of Bi-doping and y-ray irradiation on the structural and optical properties and color change of V2O5 films developed by casting/spin coating processes. Firstly, pure and Bi-doped V_2O_5 nano-sized powders with batonnets-like morphology (packs of nano-rods having diameters in the range of 7.28-16.28 nm and 9.32-95.49 nm) were prepared by a facile chemical route. The films were prepared by casting/spin-coating a suspension solution of the powder on glass substrates. X-ray diffraction (XRD) results indicate the formation of a layered V_2O_5 of orthorhombic structure, highly oriented in the (001) direction, with a crystallite size in the range of 35.8-51.3 nm, depending on the irradiation dose. The Fourier transform-infrared spectroscopy (ATR/FTIR) exhibited the presence of V-O-V, V=O vibrations, with intensities sensitive to Bi-doping and absorbed dose. Investigating the optical features reveals that the films are semitransparent. The pure V_2O_5 and Bi-doped V_2O_5 films have optical direct (indirect) band gaps in the ranges of 2.6-3.0 eV (1.3-1.6 eV) and 2.3-2.9 eV (1.1-1.5 eV), respectively. The optical parameters (k-index and the refractive index) can be tuned by Bi-doping and γ -ray doses. The CIE colorimetry was used to evaluate the CIE LAB L^* , a^* , b^* , and the total color change (ΔE) values. The results indicated that b^* and L^* can be used individually as a dosimetry index at doses \leq 30 kGy. The results illustrate the feasible controlling of V₂O₅ films by Bidoping and γ -irradiation for optoelectronic devices, dosimetry, and smart windows.

1. Introduction

Transition metal oxides exhibit unique physicochemical properties, owing to their outer *d*-electrons, and they are essential materials for various technological and biodevice (medical) applications (Shaban and El Sayed, 2020; Çarpan et al., 2024; Briceno et al., 2024). Among them, vanadium pentoxide (V₂O₅) is an *n*-type and direct/indirect gap semiconductor that can be prepared in different morphologies using physical and chemical synthetic approaches. It attracts widespread attention for energy-saving, sensing, spacecraft temperature control, screen applications, and architectural areas (color filters and reflectance mirrors), where it is preferred for thermochromic smart glasses due to its various oxidation states (V⁺², V⁺³, V⁺⁴, and V⁺⁵) and multicolor (Le et al., 2022; Peres et al., 2023; Yang et al., 2024; Chand et al., 2024). The high theoretical specific capacity of V₂O₅, and its presenting both cathodic and anodic electrochromic coloration make V₂O₅ a preferred material for electrochemical (supercapacitor) applications and as a cathode for rechargeable Li⁺ batteries (Çarpan et al., 2024; Wang et al., 2024). However, some disadvantages limit the usability and performance of V₂O₅ applications, such as the low conductivity $(10^{-3}-10^{-2} \text{ S/cm})$, low electron mobility (0.03–2.2 cm²/V·s), stability, and the expansion/-contraction of V₂O₅ during charge/discharge cycles (Yang et al., 2024; Wang et al., 2024).

The morphology, physical, chemical, and biological properties, and applications of nano-sized V_2O_5 depend on the method of preparation and doping with metals or metal oxides. Additionally, irradiating the semiconductors with γ -rays, X-rays, and high-energy particles results in ionization, atomic displacement, vacancies, or dislocations, which create energy levels inside the band gap and trapping or recombination centers for the charge carriers. The material could transform from crystalline to a partial amorphization (due to defect formation) and then recrystallize with increasing the dose due to the associated heating effect. According to Khan et al. (2016), the spin-coated monoclinic VO₂ films converted to an amorphous state upon irradiation with 200 MeV

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